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# 2SB860

Silicon PNP Triple Diffused

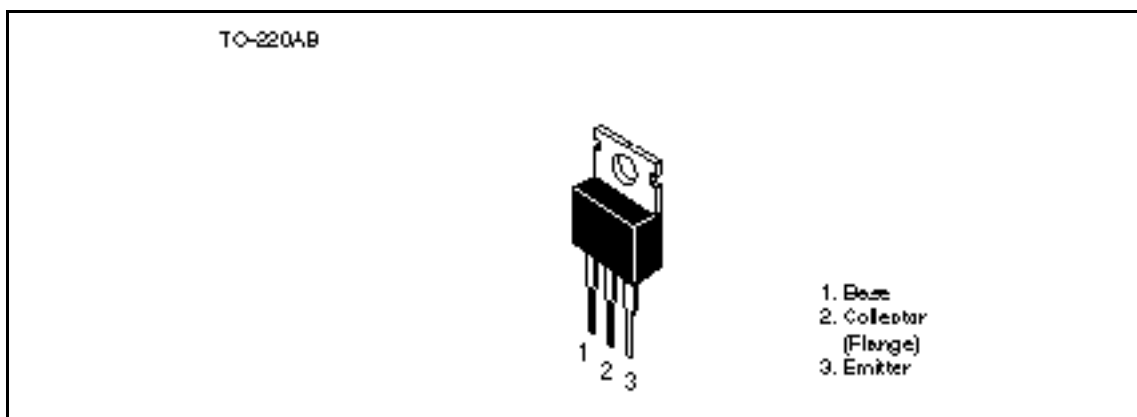
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## Application

Low frequency power amplifier TV vertical deflection output complementary pair with 2SD1137

## Outline



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-100	V
Collector to emitter voltage	$V_{CEO}$	-100	V
Emitter to base voltage	$V_{EBO}$	-4	V
Collector current	$I_C$	-4	A
Collector peak current	$I_{C(peak)}$	-5	A
Collector power dissipation	$P_C$	1.8	W
	$P_C^{*1}$	40	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-45 to +150	°C

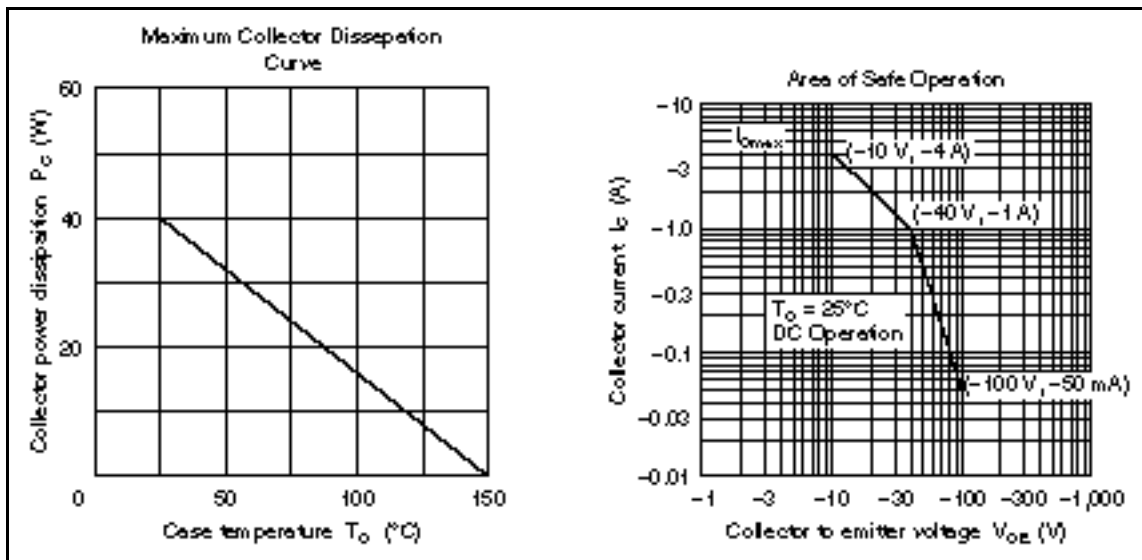
Note: 1. Value at  $T_C = 25^\circ\text{C}$

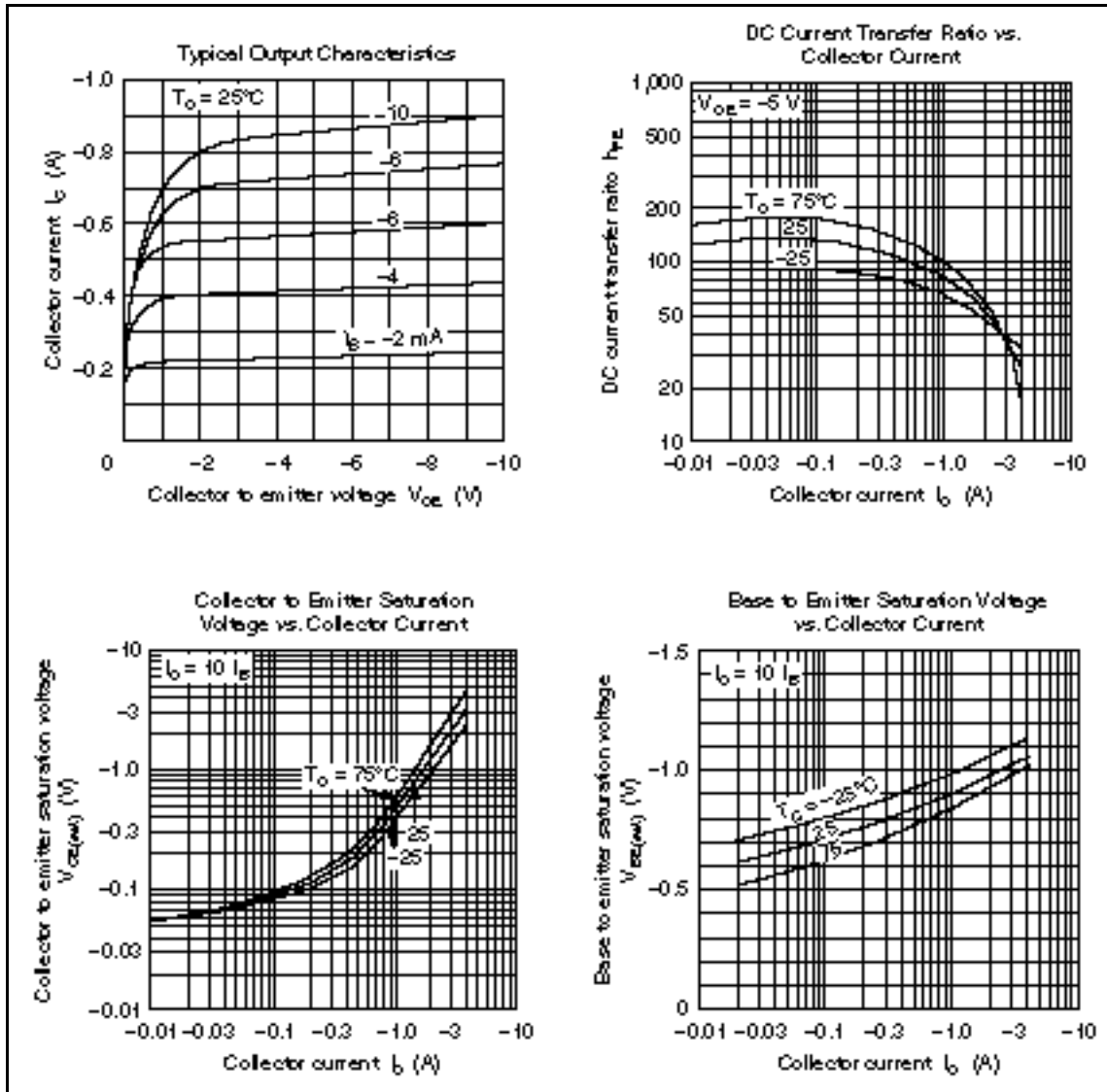
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### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	V	$I_C = -10 \text{ mA}$ , $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	—	—	V	$I_E = -1 \text{ mA}$ , $I_C = 0$
Collector cutoff current	$I_{CEO}$	—	—	-100	$\mu\text{A}$	$V_{CE} = -80 \text{ V}$ , $R_{BE} =$
Emitter cutoff current	$I_{EBO}$	—	—	-50	$\mu\text{A}$	$V_{EB} = -3.5 \text{ V}$ , $I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1.0	V	$I_C = -1 \text{ A}$ , $I_B = -0.1 \text{ A}^{*1}$
DC current transfer ratio	$h_{FE}$	50	—	250		$V_{CE} = -4 \text{ V}$ $I_C = -0.5 \text{ A}^{*1}$
		25	—	350		$I_C = -50 \text{ mA}$

Note: 1. Pulse test





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